

High Frequency NPN Transistor Array

The CA3127 consists of five general purpose silicon NPN transistors on a common monolithic substrate. Each of the completely isolated transistors exhibits low 1/f noise and a value of f_T in excess of 1GHz, making the CA3127 useful from DC to 500MHz. Access is provided to each of the terminals for the individual transistors and a separate substrate connection has been provided for maximum application flexibility. The monolithic construction of the CA3127 provides close electrical and thermal matching of the five transistors.

Ordering Information

PART NUMBER	PART MARKING	TEMP. RANGE (°C)	PACKAGE	PKG. DWG. #
CA3127M	CA3127	-55 to 125	16 Ld SOIC	M16.15
CA3127MZ (Note)	CA3127MZ	-55 to 125	16 Ld SOIC (Pb-free)	M16.15

NOTE: Intersil Pb-free plus anneal products employ special Pb-free material sets; molding compounds/die attach materials and 100% matte tin plate termination finish, which are RoHS compliant and compatible with both SnPb and Pb-free soldering operations. Intersil Pb-free products are MSL classified at Pb-free peak reflow temperatures that meet or exceed the Pb-free requirements of IPC/JEDEC J STD-020.

Features

- Gain Bandwidth Product (f_T) >1GHz
- Power Gain 30dB (Typ) at 100MHz
- Noise Figure. 3.5dB (Typ) at 100MHz
- Five Independent Transistors on a Common Substrate
- Pb-Free Plus Anneal Available (RoHS Compliant)

Applications

- VHF Amplifiers
- Multifunction Combinations - RF/Mixer/Oscillator
- Sense Amplifiers
- Synchronous Detectors
- VHF Mixers
- IF Converter
- IF Amplifiers
- Synthesizers
- Cascade Amplifiers

Pinout

